

[DEVICE AND METHOD FOR BREAKING LEAKAGE CURRENT PATH OF MEMORY DEVICE AND STRUCTURE OF MEMORY DEVICE]

Abstract

A device and a method for breaking leakage current path caused by a defect in a memory cell of a memory array are disclosed. The device includes a first breaking circuit and a second breaking circuit. When at least one memory cell is failed, the first breaking circuit can disconnect the connection between the bit line and the power supplying terminal and the connection between the bit line bar and the power supplying terminal. Moreover, the second breaking circuit can disconnect the connection between the bit line and the sense amplifier and the connection between bit line bar and the sense amplifier. Accordingly, the leakage current from the power supplying terminal to the defective memory cell can be eliminated.